

Semiconductor optoelectronics 1

Optoelectronic devices and photodetectors

Modern physics for engineers

David Miller

Optoelectronic devices

Optoelectronic devices



Being able to convert
easily and efficiently between
light and electrical power and
signals
has transformed what we can do
with light

The devices that enable such
conversions are called
optoelectronic devices

Optoelectronic devices

Viewed broadly, optoelectronics includes

- conventional incandescent and fluorescent light bulbs
- vacuum-based devices like cathode ray tube and plasma displays and some specialized photodetectors (e.g., photomultiplier tubes)
- liquid crystal display technology
- and, especially now
 - semiconductor optoelectronics
 - which we can now understand

Optoelectronic devices



Many optoelectronic devices use diodes, but in different ways

- collecting electrons and holes generated by absorbing photons, in, e.g.,
 - **solar cells**
 - **photodetectors for signals on light beams**

Optoelectronic devices

- injecting electrons and holes into the junction region
 - by forward biasing the diodes so they can recombine by emitting photons for
 - light-emitting diodes
 - e.g., illumination
 - semiconductor lasers
 - e.g., fiber communications

Optoelectronic devices



- applying large electric fields inside devices without much current by reverse biasing

We use this for several kinds of light modulators to turn light beams on and off in optical communications by changing the material's optical properties, such as optical absorption strength or refractive index

Optoelectronic devices



Here we will introduce especially
the use of diode structures in
detection
and
light emission

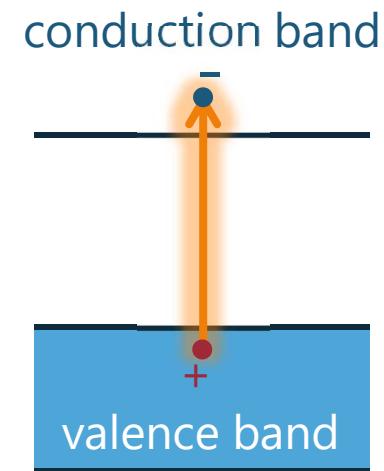
Photoconductors

Generating electron-hole pairs

Absorbing a photon in a semiconductor with photon energy greater than the band gap energy can take an electron from the valence band and put it in the conduction band leaving a hole in the valence band

We can call this process generation of an “electron-hole pair”

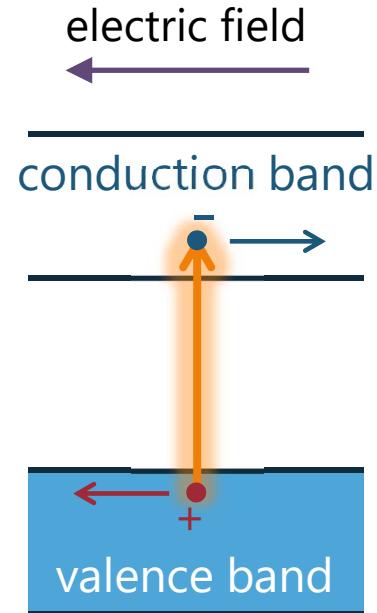
These “photogenerated” electrons and holes are sometimes called “photocarriers”



Photoconductors

Before the electron and hole
“recombine”
with the electron falling back into
the valence band
they can conduct electricity

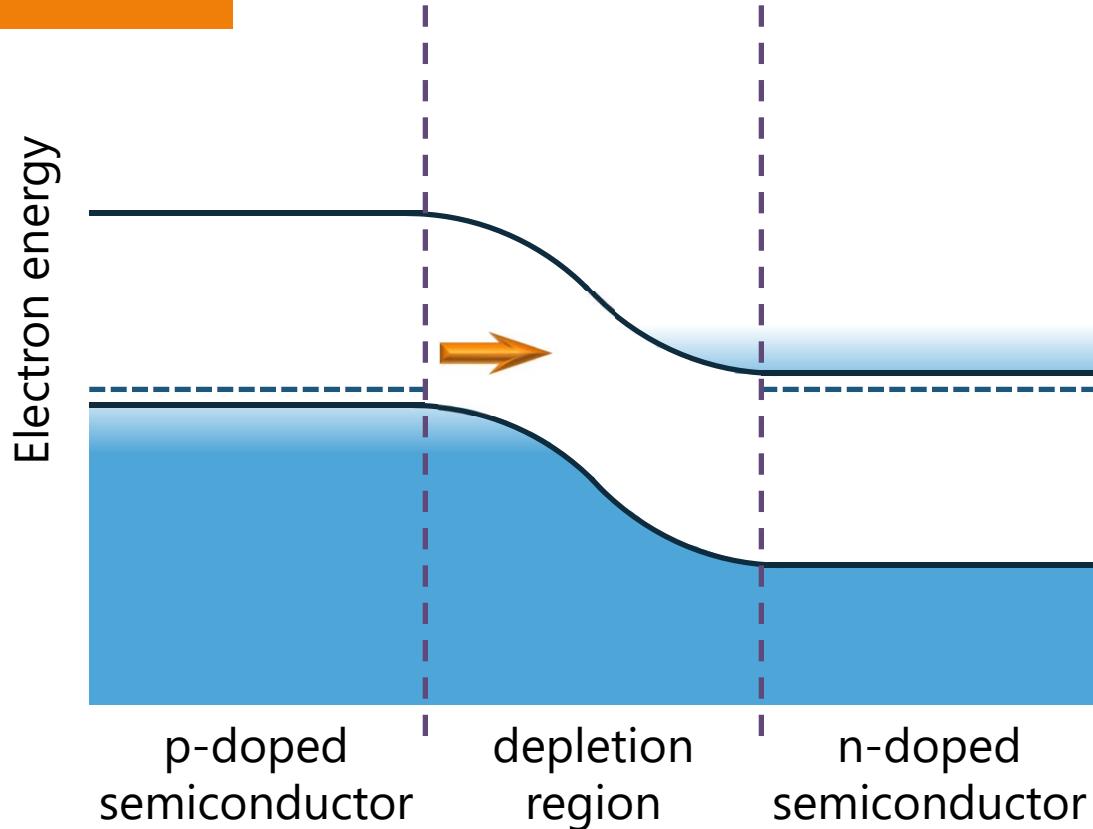
In a piece of semiconductor
this is called photoconduction
This process is used
for some photodetectors



Photodiodes

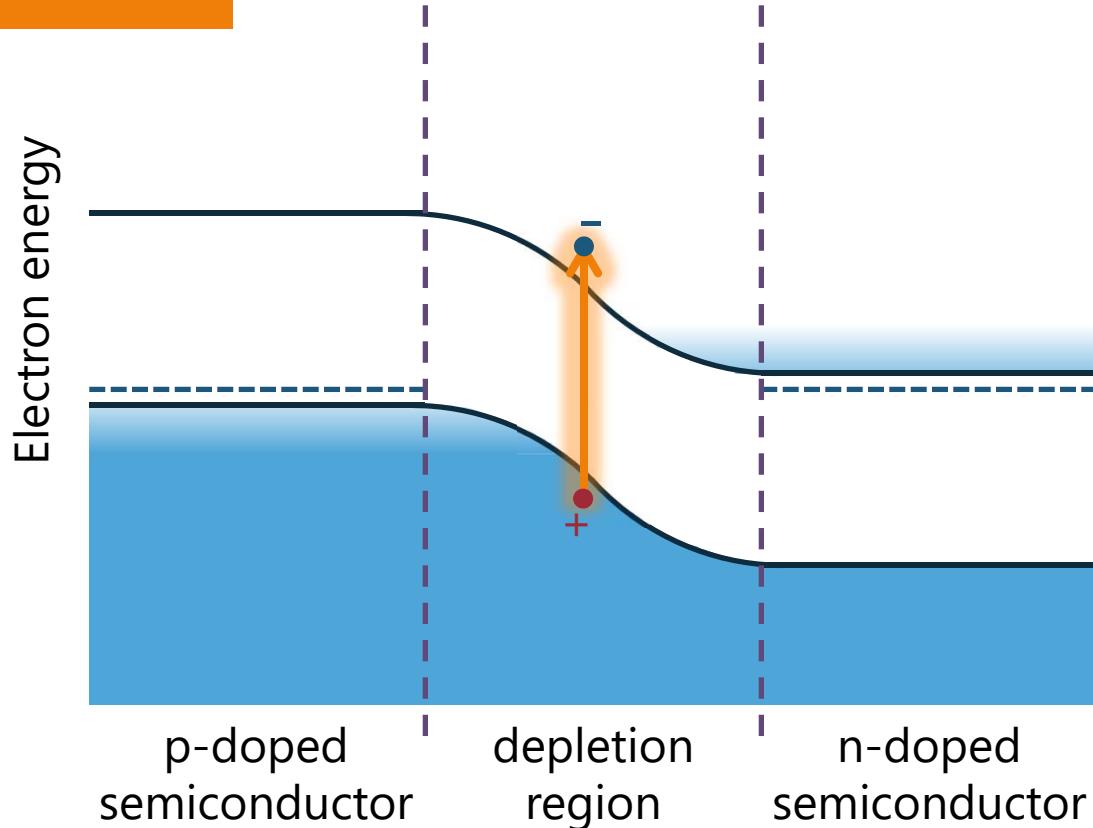
Photocarriers in diodes

Absorbing a photon in the depletion region



Photocarriers in diodes

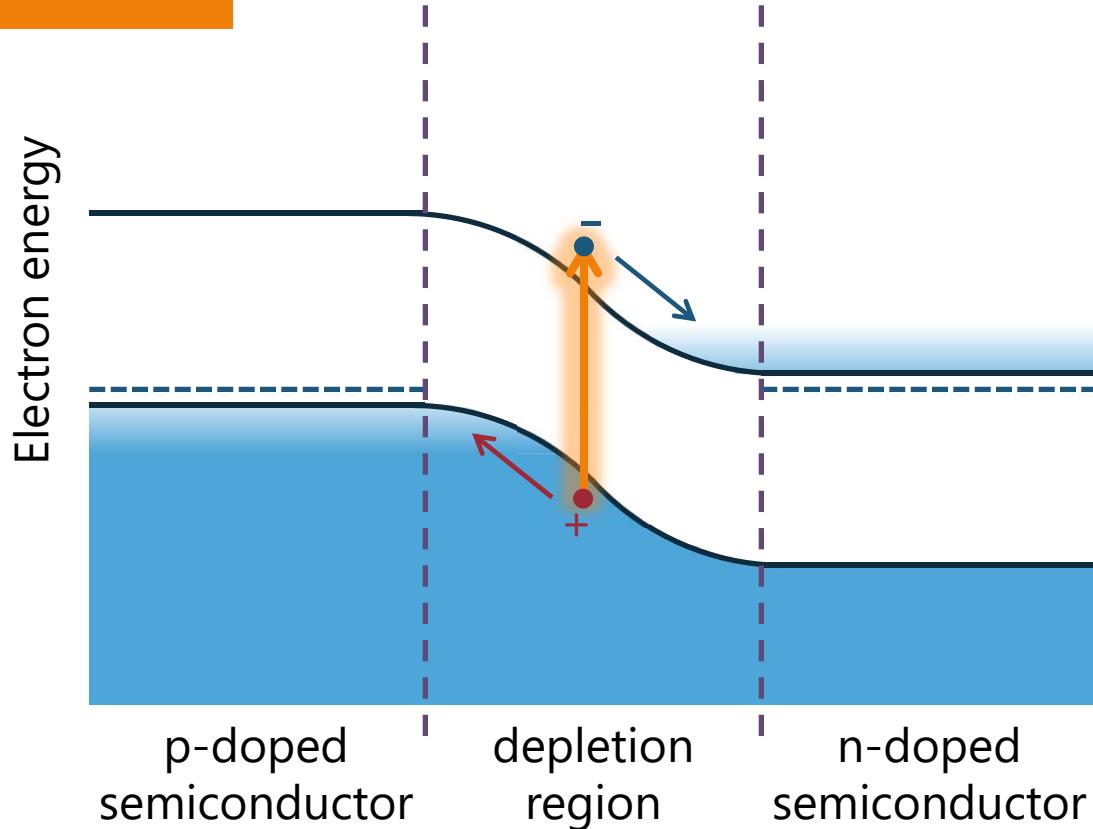
Absorbing a photon in
the depletion region
generates an
“electron-hole” pair



Photocarriers in diodes

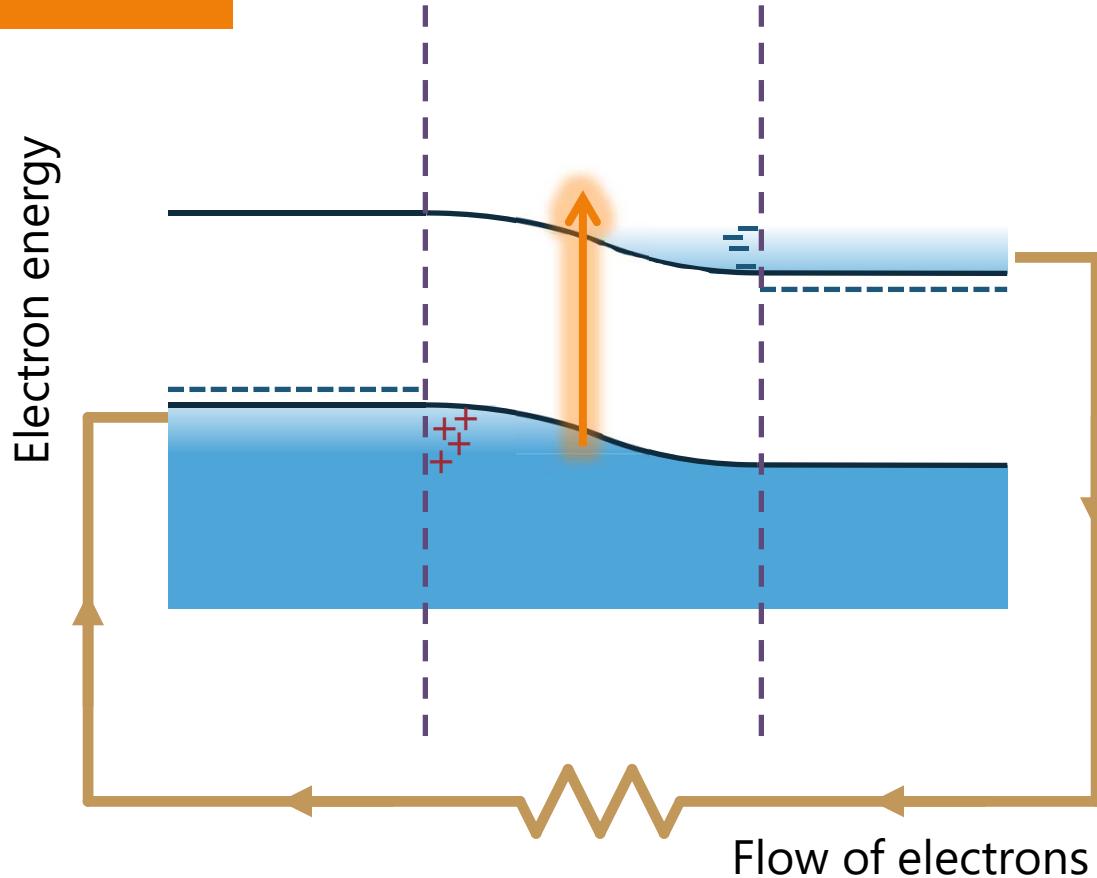
Absorbing a photon in the depletion region generates an “electron-hole” pair

The electron and hole drift “downhill” in the field



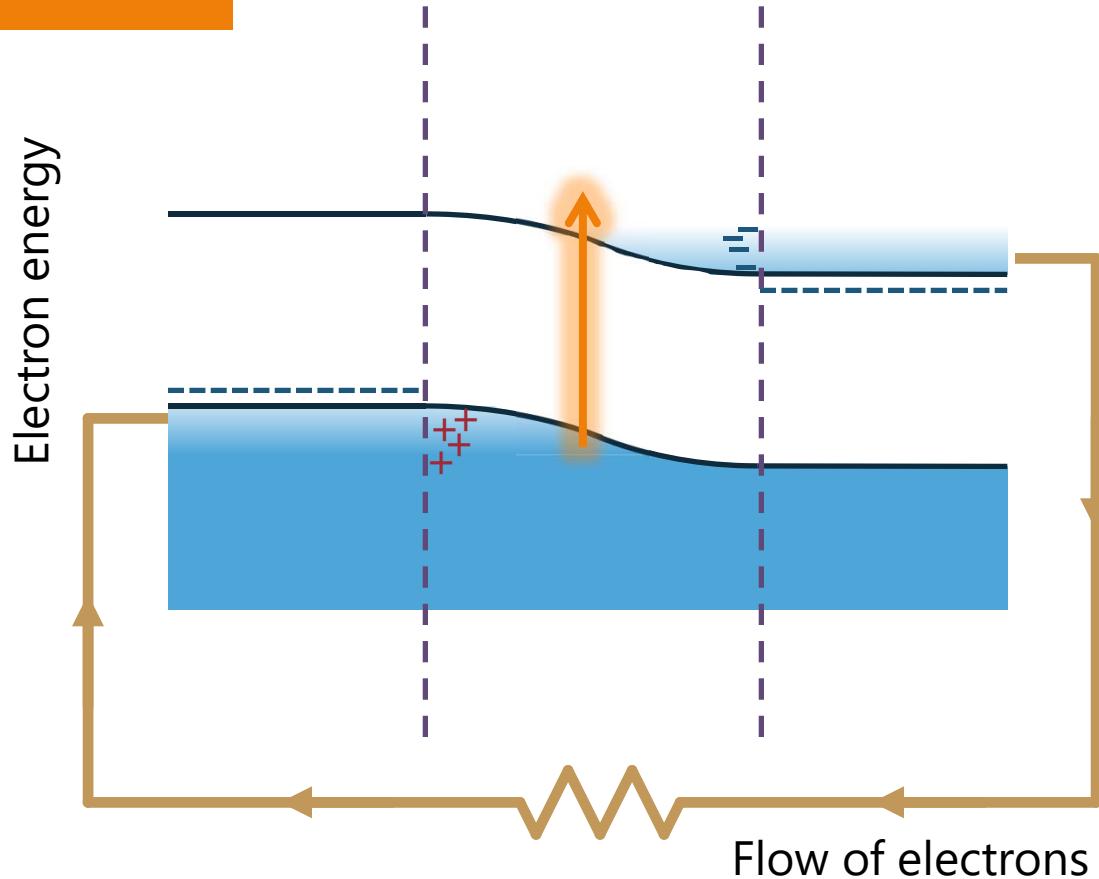
Photovoltaic diode

The charge separation creates a potential to resist the charge separation which creates an external voltage which can drive a current through a resistor



Photovoltaic diode

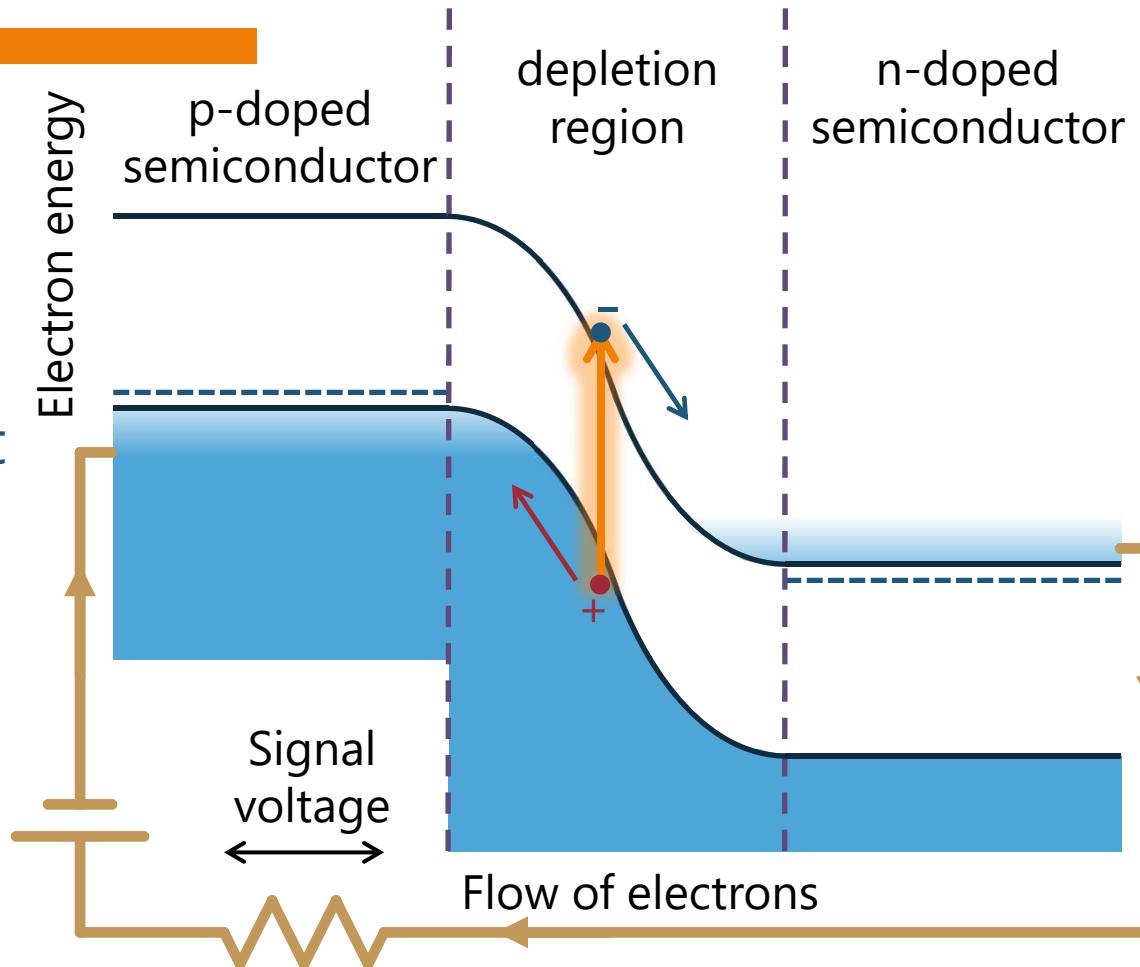
This generates electric power in a solar cell and gives an output voltage for a photovoltaic photodetector



Reverse-biased photodiode

In a reverse-biased photodiode
photogenerated
electrons and holes
are rapidly swept out
by the electric field

This gives a
photocurrent in an
external circuit
and a signal voltage
over a resistor



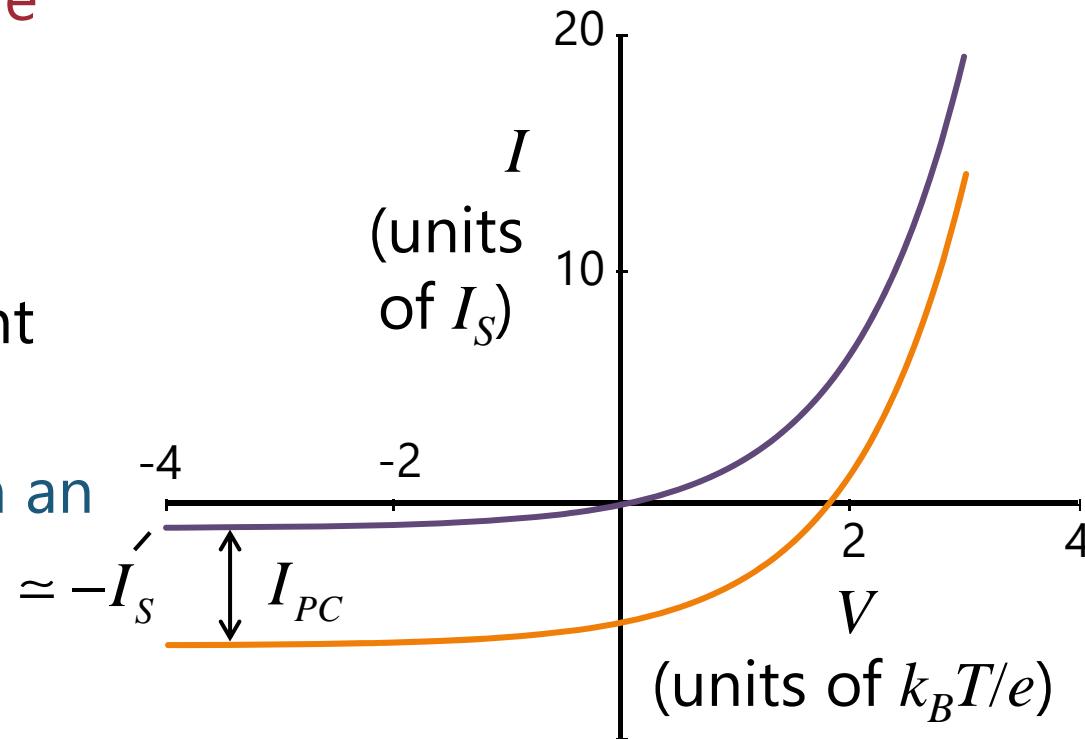
Diode current-voltage (I-V)

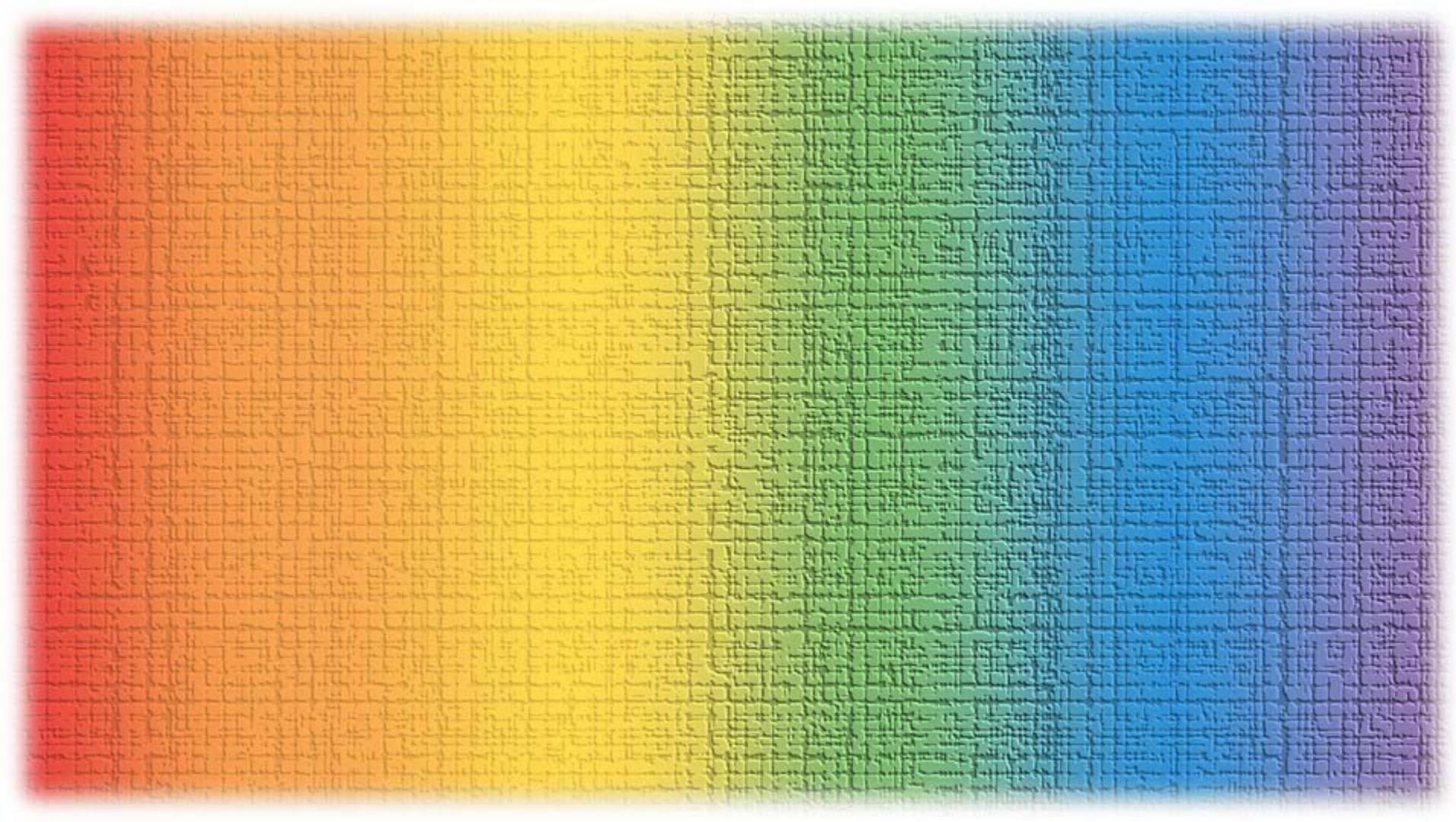
With light

the current-voltage curve
is shifted down by the
magnitude of the
photocurrent I_{PC}

In the lower right quadrant
power $|V \times I|$
would be generated in an
external resistor
as in a solar cell

$$I = I_S \left[\exp\left(\frac{eV}{k_B T}\right) - 1 \right] - I_{PC}$$





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Light emission

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Thermal and non-thermal light sources

Thermal and non-thermal light sources

From the Boltzmann factor
at any finite temperature

$$\frac{N_2}{N_1} = \exp\left(-\frac{E_2 - E_1}{k_B T}\right)$$

there are always more systems in the lower state
than in the upper state

so a photon coming into the system

is more likely to be absorbed – $B_{12}N_1\rho(\nu)$

than it is to stimulate emission – $B_{12}N_2\rho(\nu)$

Hence photon loss exceeds photon gain for a system in
thermal equilibrium

so stimulated emission does not “run away” to lasing

Thermal and non-thermal light sources



There is still emission from warm bodies

both spontaneous $A_{21}N_2$

and even some stimulated $B_{12}N_2\rho(\nu)$

though that is normally a small fraction

These are the normal processes of “thermal” emission of light from hot objects

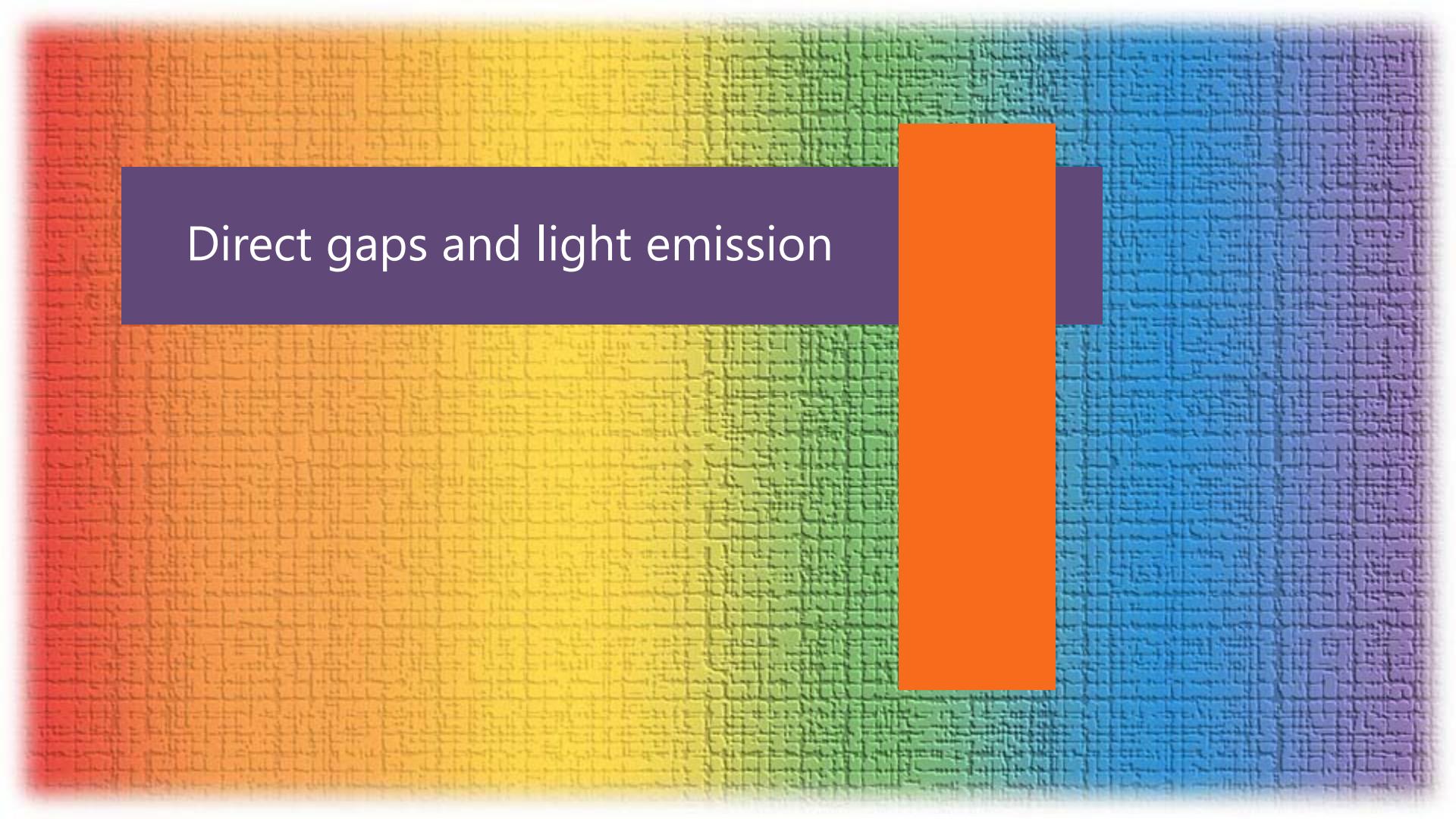
Thermal and non-thermal light sources



If by some non-thermal process, we can put some of the “atoms” in their upper states

we can get light emission without high temperatures

as in light emitting diodes and lasers



Direct gaps and light emission

Direct gap semiconductor

If the lowest minimum in the conduction band

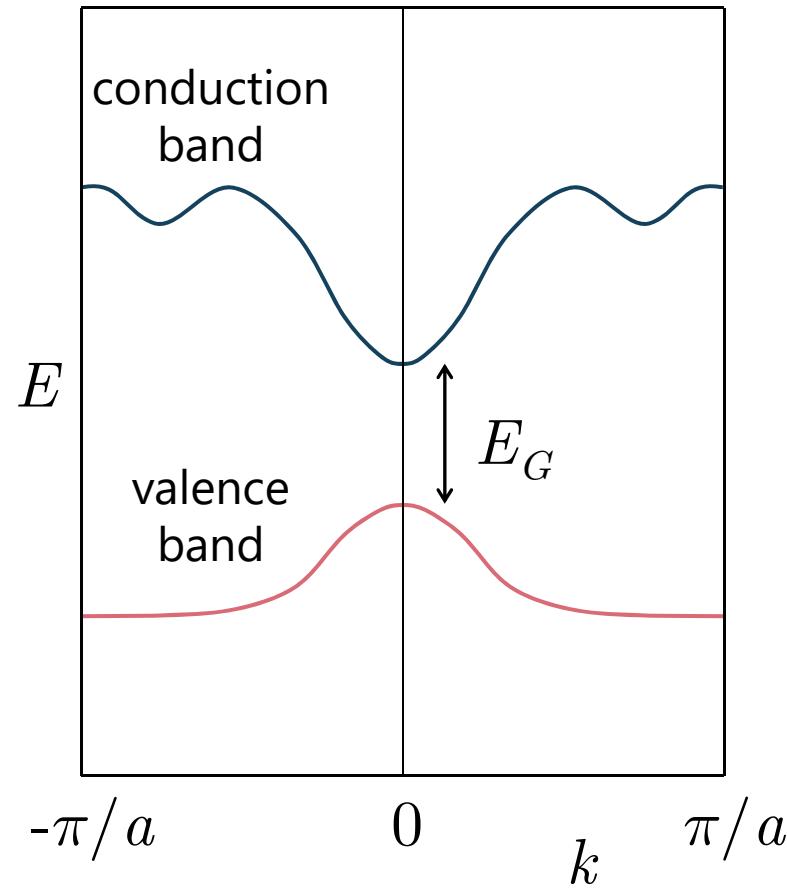
lies directly above

the highest maximum in the valence band

the semiconductor is said to

have a

"direct gap"



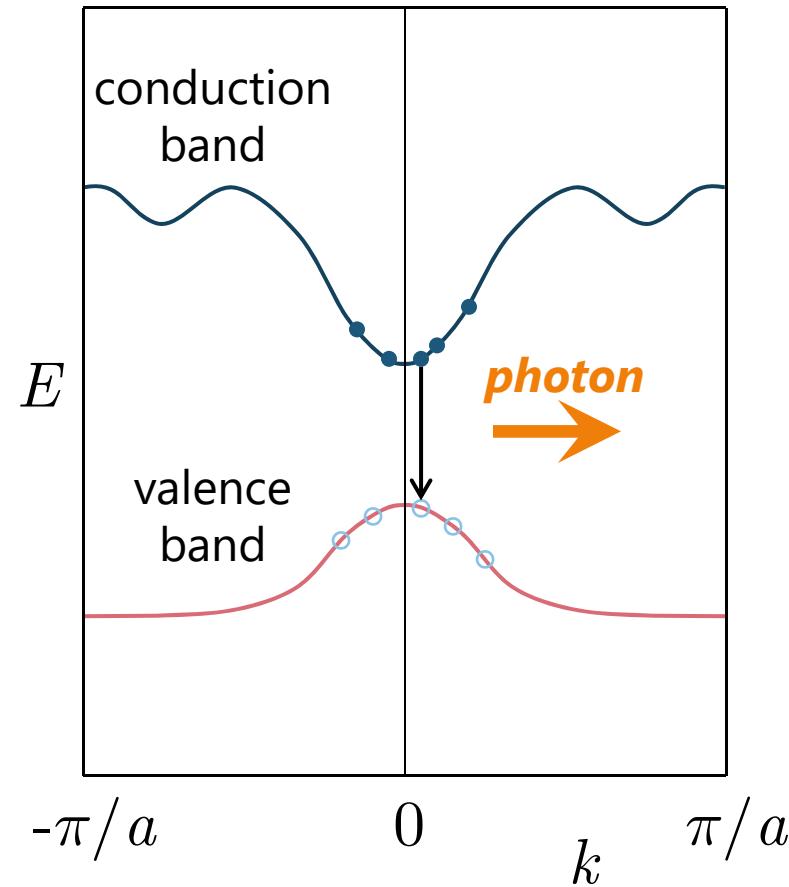
Direct gap semiconductor

Direct gaps are important for light emitters

Electrons “pumped” into the conduction band gather in the lowest minimum

“Holes” pumped into the valence band gather in the highest maximum

An electron can fall “vertically” to fill in a hole beneath it emitting light



Indirect gap semiconductor

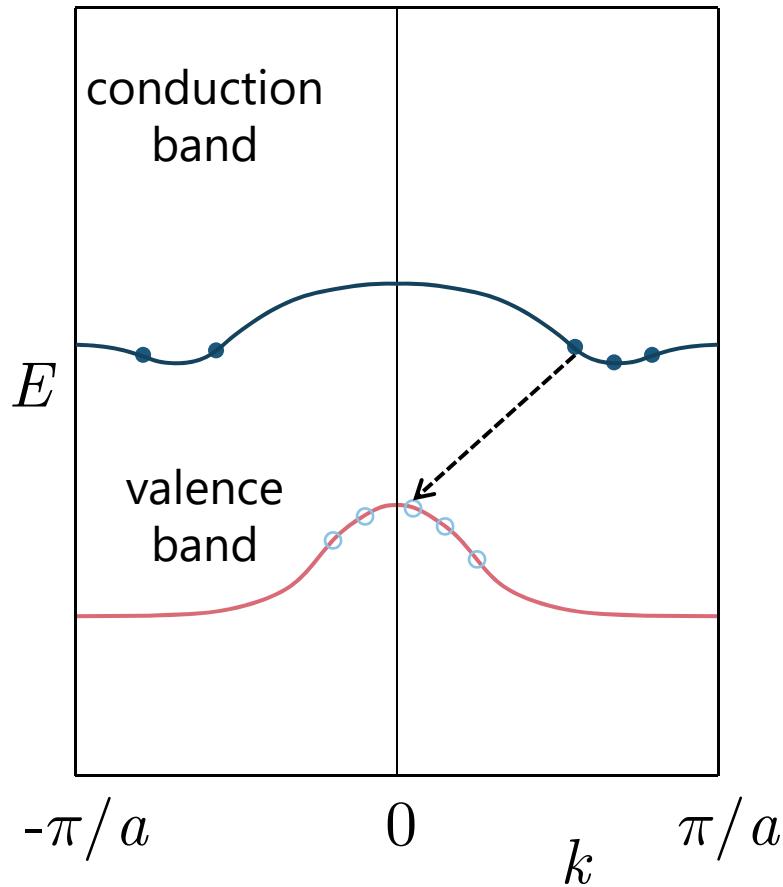
In an indirect gap semiconductor

e.g., silicon, germanium

the lowest conduction band minimum (or minima) is (are) not directly above the highest valence band maximum

Light emission is weak

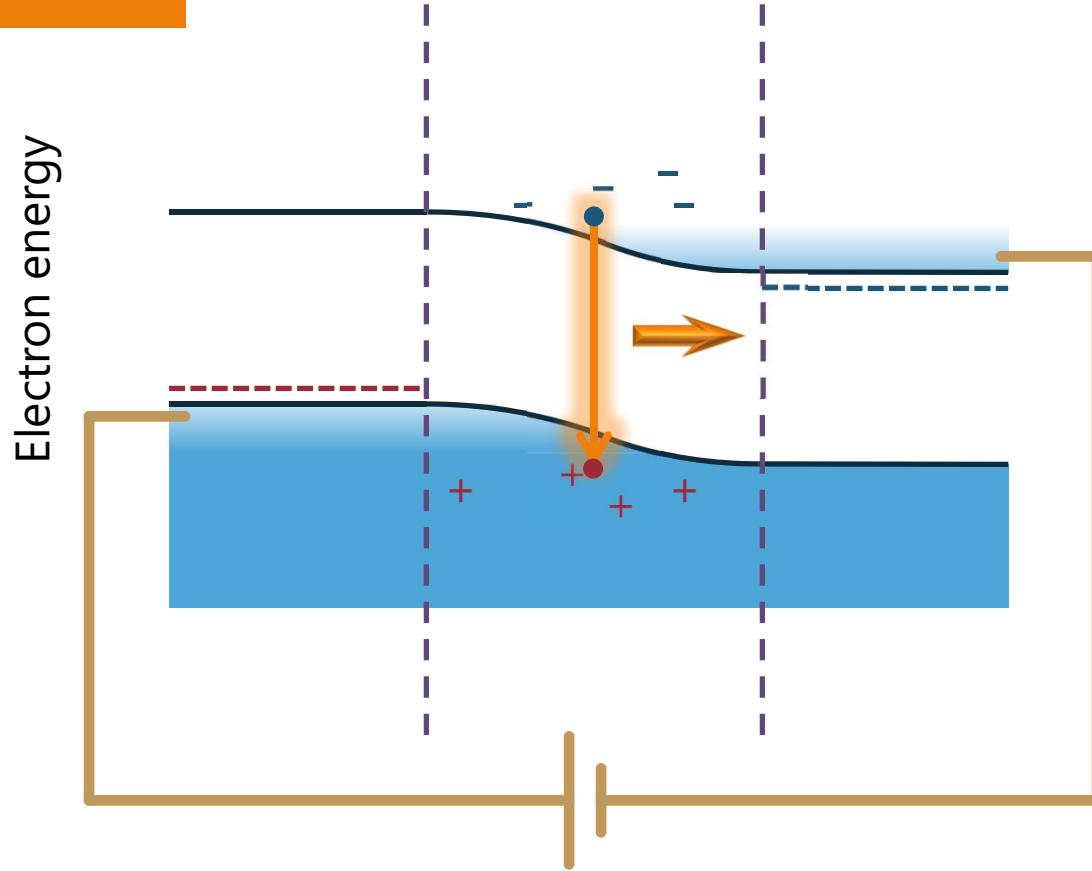
“non-vertical” transitions by emission of photons are weak



Forward-biased diode light emitters

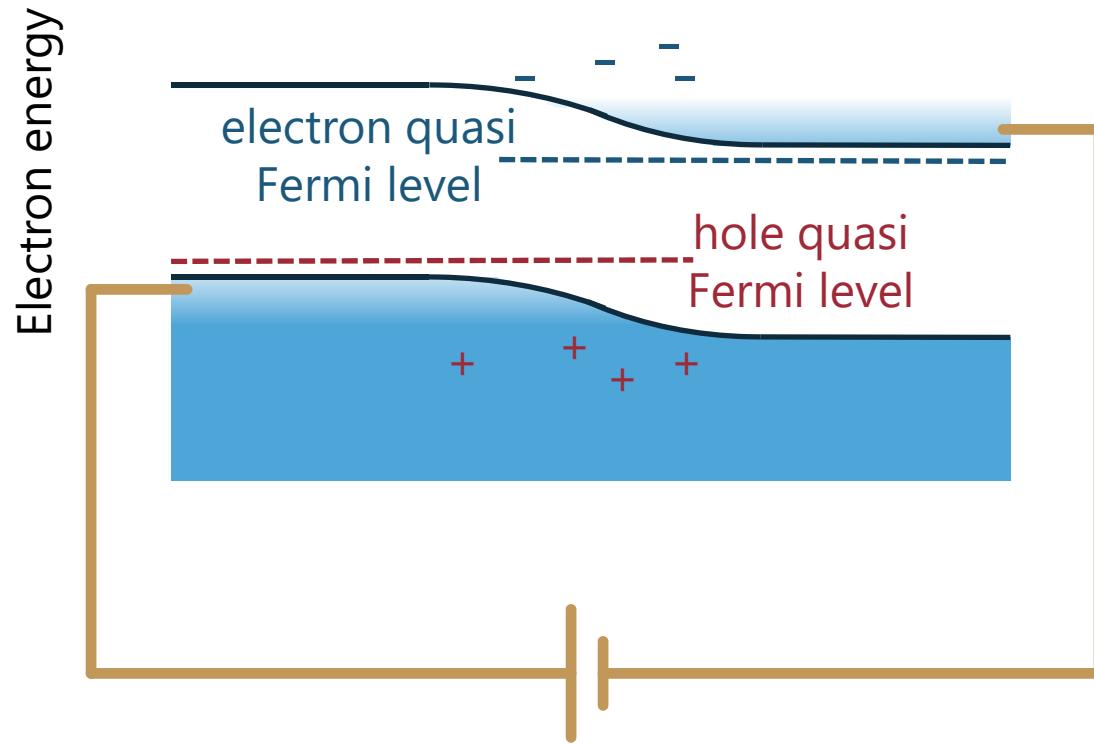
Forward-biased light emitter

Forward biasing the diode
injects
electrons
and
holes
into the same region
where they can
recombine
to emit light



Forward-biased light emitter

Under forward bias
electrons and holes
near the junction
can effectively have
their own Fermi
levels
different from each
other
known as quasi
Fermi levels



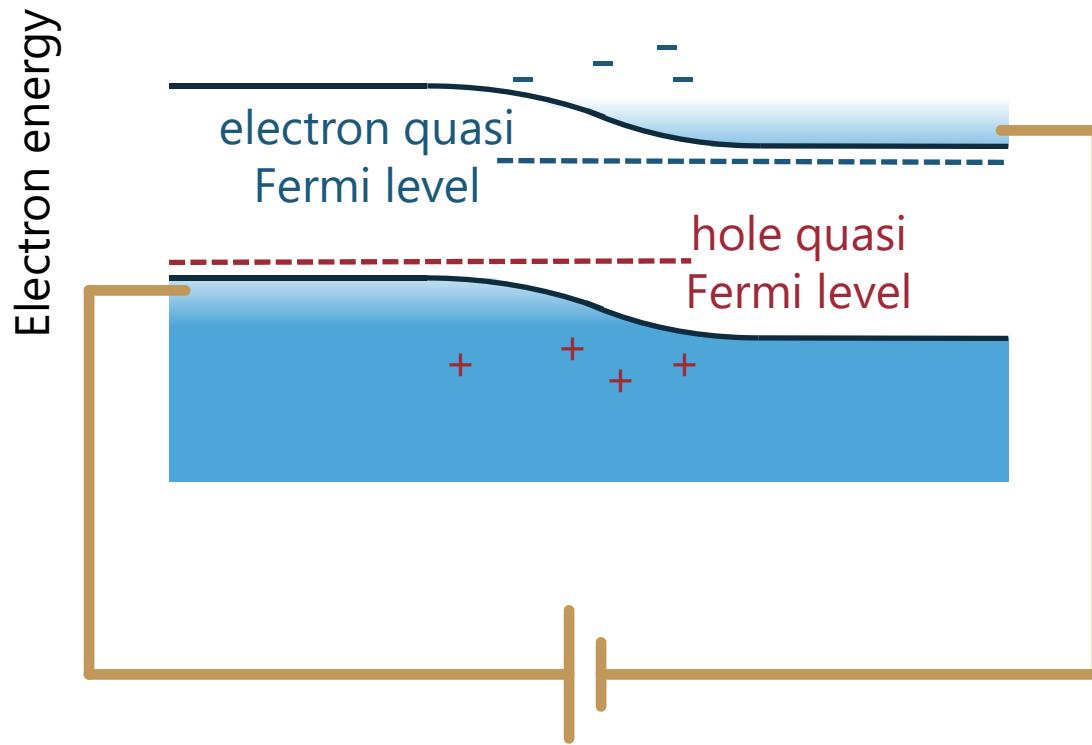
Forward-biased light emitter

The electrons can be in thermal equilibrium with each other

and so can the holes giving useful models for their distributions

This allows detailed models for

light emission by “recombination”



Light-emitting diode emission

For light emitting diodes
it is sufficient to get some
electrons in the conduction
band
and some holes in the
valence band
Then recombination can
happen
emitting photons

